VERSION SHOWING THE CHANGES TO THE CLAIMS

This listing replaces all prior listings of the claims.

1 (Currently amended). An electronic organic component comprising at least two functional layers adjacent to one another, the first functional layer being produced from the same organic material as the second and adjacent functional layer and having the same chemical properties, but differing at least partly therefrom in its electrical physical properties .

2 (Previously presented). The electronic organic component as claimed in claim 1, in which one of the functional layers is semiconductive, the semiconductive functional Layer and at least one other functional layer differ only in their redox potential.

3 (Currently amended). A method for the production of an organic electronic component, in which two different functional layers are produced in a single process step having the same chemical properties, but different electrical properties, by converting a part of a functional layer into another different functional layer by modification of the material by partial reaction.

4 (Previously presented). The method as claimed in claim 3, in which electrodes and/or conductor tracks and a semiconductive functional layer are produced with structuring in one process step and in one functional layer.

5 (Previously presented). The method as claimed in claim 3 wherein one of the functional layers is a semiconductive layer, in which a conductive structure is introduced in a controlled manner into the semiconductive functional layer by partial covering and treatment of the uncovered regions with a redox composition.

6 (Previously presented). The method as claimed in claim 3, in which one of the functional layers is a semiconductive layer and the semiconductive layer is covered by a photoresist.

7 (Previously presented). The method as claimed in claim 5 , in which the redox composition is partially applied to the semiconductive functional layer by printing.

8 (Previously presented). The method as claimed in claim 3 , in which a time-stable partial oxidation of the semiconductive functional layer is carried out by an oxidizing agent.

9 (Previously presented). The method as claimed in claim 4, in which a conductive structure is introduced in a controlled manner into the semiconductive functional layer by partial covering and treatment of the uncovered regions with a redox composition.

10 (Previously presented). The method as claimed in claim 4 in which the semiconductive layer is covered by a photoresist.

11 (Previously presented). The method as claimed in claim 5 in which the semiconductive layer is covered by a photoresist.

12 (Previously presented). The method as claimed in claim 3 wherein one of the functional layers is a semiconductive functional layer in which a redox composition is partially applied to the semiconductive functional layer by printing.

13 (Previously presented). The method as claimed in claim 4 in which a redox composition is partially applied to the semiconductive functional layer by printing.

14. (Previously presented). The method as claimed in claim 6 in which a redox composition is partially applied to the semiconductive functional layer by printing.

15 (Previously presented). The method as claimed in claim 4 in which a time-stable partial oxidation of the semiconductive functional layer is carried out by an oxidizing agent.

16 (Previously presented). The method as claimed in claim 5 in which a time-stable partial oxidation of the semiconductive functional layer is carried out by an oxidizing agent.

17 (Previously presented). The method as claimed in claim 6 in which a time-stable partial oxidation of the semiconductive functional layer is carried out by an oxidizing agent.

18 (Previously presented). The method as claimed in claim 7 in which a time-stable partial oxidation of the semiconductive functional layer is carried out by an oxidizing agent.